

IN THE SPECIFICATION

Please replace the paragraph beginning at page 5, line 11, with the following rewritten paragraph:

The method includes: using the mask with the repeated pattern, for example, having a pattern width of 2  $\mu\text{m}$  and pitch of 0.3  $\mu\text{m}$  formed thereon to form, for example, a polycrystal having a length of 2  $\mu\text{m}$  and width of 0.3  $\mu\text{m}$ .